

7th JSPS Silicon Symposium Timetable

Nov. 21 (Mon)	Nov. 22 (Tue)	Nov. 23 (Wed)	Nov. 24 (Thu)	Nov. 25 (Fri)
	Morning 8:30-11:45 Opening Remarks 8:30-8:40 85 min 8:40-10:05 Plenary I (1) A-1 H. Furuya 35 min Crystal Growth and Wafer Technology I (2) B-1 G. Kissinger 25 min B-2 W. Sugimura 25 min Coffee Break 10:05-10:30 75 min 10:30-11:45 Crystal Growth and Wafer Technology II (3) C-1 H. Sudo 25 min C-2 K. Kurita 25 min C-3 J. Park 25 min Lunch Break 11:45-13:20 Afternoon 13:20-16:40 100 min 13:20-15:00 Advanced Characterization Technology I (4) D-1 H. C. Alt 25 min D-2 Y. Imai 25 min D-3 T. Schüllli 25 min D-4 V. P. Markevich 25 min Coffee Break 15:00-15:25 75 min 15:25-16:40 Advanced Characterization Technology II (3) E-1 J. Lagowski 25 min E-2 M. Furuta 25 min E-3 H. Yamada-Kaneta 25 min Break 16:40-17:00 57 min (3 min/paper) 17:00-17:57 Short Presentation for Poster F-1 T. Fukuda F-11 W. Fukushima F-2 Y. Sano F-12 A. Onaka-Masada F-3 M. Porrini F-13 A. Yamada F-4 H. Habuka F-14 Y. Hada F-5 H. Suzuki F-15 H. Fukuda F-6 T. Taishi F-16 S. Yamaoka F-7 Y. Ino F-17 K. Kobayashi F-8 H. Kiuchi F-18 W. Takeuchi F-9 K. Shida F-19 J. Inagaki F-10 K. Omote Dinner Break 17:57-19:30 Evening 19:30-22:00 30 min 19:30-20:00 After Dinner Talk I (1) (Memorial for Prof.Rozgonyi) G-1 K. Sueoka, J. Park, T. Ono 30 min Poster Presentation (F) 20:00-22:00 Posters F-1 ~ F-19	Morning 8:30-12:05 100 min 8:30-10:10 Defects and Impurities I (4) H-1 T. Maeta 25 min H-2 S. Cottenier 25 min H-3 H. Yoshida 25 min H-4 N. Fukata 25 min Coffee Break 10:10-10:25 100 min 10:25-12:05 Defects and Impurities II (4) I-1 M. Stavola 25 min I-2 M. D. McCluskey 25 min I-3 B. G. Svensson 25 min I-4 T. Ono 25 min Optional Tour available	Morning 8:30-11:40 85 min 8:30-9:55 Plenary II (1) J-1 B. Sopori 35 min Photovoltaic Si I (2) K-1 O. Isabella 25 min K-2 J. Weber 25 min Coffee Break 9:55-10:25 75 min 10:25-11:40 Photovoltaic Si II (3) L-1 M. Tajima 25 min L-2 S. Binetti 25 min L-3 K. Kakimoto 25 min Lunch Break 11:40-13:30 Afternoon 13:30-16:05 75 min 13:30-14:45 Photovoltaic Si III (3) M-1 S. Ostapenko 25 min M-2 T. Suemasu 25 min M-3 R. Sinton 25 min Coffee Break 14:45-15:15 50 min 15:15-16:05 Group IV Semiconductor-based Device Technology I (2) N-1 J. O. Borland 25 min N-2 S. Nishizawa 25 min Break 16:05-16:40 60 min (3 min/paper) 16:40-17:40 Short Presentation for Poster O-1 H. Mori O-11 S. Kawachi O-2 T. Sugiura O-12 T. Ito O-3 Y. Ohshita O-13 Y. Mizuta O-4 R. Yokogawa O-14 H. Nakane O-5 T. Shimura O-15 R. Miyagawa O-6 M. Tomita O-16 T. Akiyama O-7 H. Koyama O-17 S. Nakano O-8 K. Toyosaki O-18 M. Uchino O-9 K. Tadano O-19 T. Shimizu O-10 Y. Ishikawa O-20 K. Suzuki Dinner Break 17:40-19:30 Evening 19:30-22:00 30 min 19:30-20:00 After Dinner Talk II (1) P-1 H. Richter 30 min Poster Presentation (O) 20:00-22:00 Posters O-1 ~ O-20	Morning 8:30-12:10 50 min 8:30-9:20 Group IV Semiconductor-based Device Technology II (2) Q-1 K. Wada, Y. Ishikawa 25 min Q-2 Y. Moriyama 25 min 50 min 9:20-10:10 SiC, Nitride semiconductors and other wide-bandgap materials I (2) R-1 Y. Honda 25 min R-3 S. Fujita 25 min Coffee Break 10:10-10:40 75 min 10:40-11:55 SiC, Nitride semiconductors and other wide-bandgap materials II (3) S-1 B. Raghathamachar 25 min S-2 H. Tsuchida 25 min S-3 P. Bergman 25 min Closing Remarks 11:55-12:10 Farewell Dinner
REGISTRATION				
Desk Opening 16:00-20:00				
Get Together Party 18:00-20:00				